



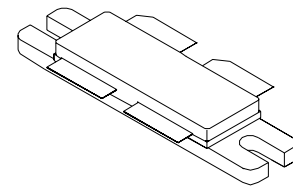
SD57120

RF POWER TRANSISTORS

The LdmoST FAMILY

N-CHANNEL ENHANCEMENT-MODE LATERAL MOSFETs

- EXCELLENT THERMAL STABILITY
- COMMON SOURCE CONFIGURATION, PUSH-PULL
- $P_{OUT} = 120\text{ W}$ WITH 13 dB gain @ 960 MHz
- BeO FREE PACKAGE
- INTERNAL INPUT MATCHING



M252
epoxy sealed

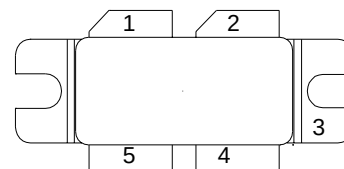
ORDER CODE
SD57120

BRANDING
TSD57120

DESCRIPTION

The SD57120 is a common source N-Channel enhancement-mode lateral Field-Effect RF power transistor designed for broadband commercial and industrial applications at frequencies up to 1.0 GHz. The SD57120 is designed for high gain and broadband performance operating in common source mode at 28 V. Its internal matching makes it ideal for base station applications requiring high linearity.

PIN CONNECTION



1. Drain
2. Drain
3. Source

4. Gate
5. Gate

ABSOLUTE MAXIMUM RATINGS ($T_{CASE} = 25\text{ }^{\circ}\text{C}$)

Symbol	Parameter	Value	Unit
$V_{(BR)DSS}$	Drain-Source Voltage	65	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current	14	A
P_{DISS}	Power Dissipation (@ $T_c = 70\text{ }^{\circ}\text{C}$)	236	W
T_J	Max. Operating Junction Temperature	200	$^{\circ}\text{C}$
T_{STG}	Storage Temperature	-65 to +150	$^{\circ}\text{C}$

THERMAL DATA

$R_{th(j-c)}$	Junction -Case Thermal Resistance	0.55	$^{\circ}\text{C/W}$
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ELECTRICAL SPECIFICATION (T_{CASE} = 25 °C)

STATIC (Per Section)

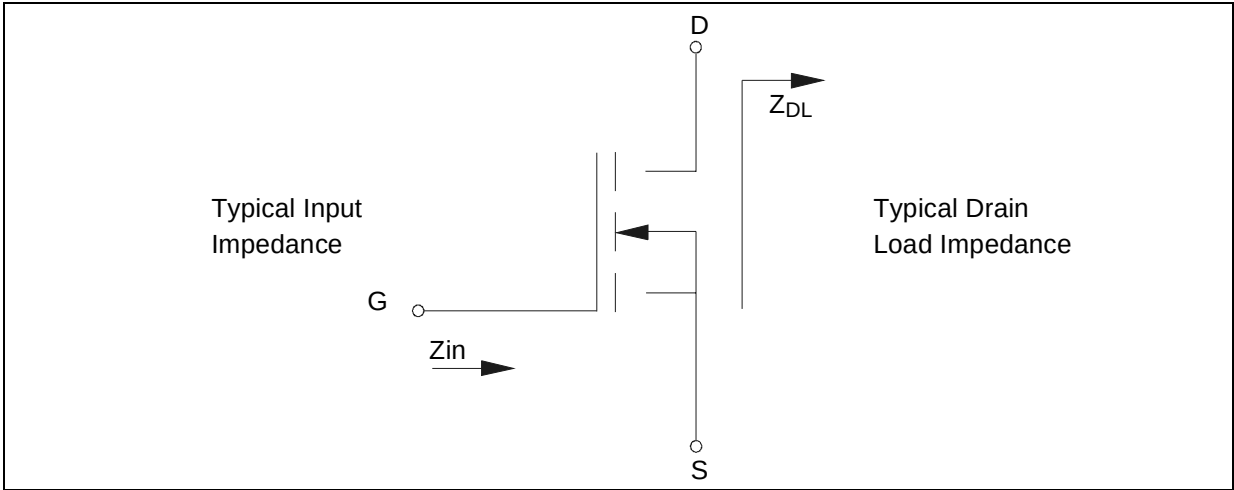
Symbol	Test Conditions		Min.	Typ.	Max.	Unit
V _{(BR)DSS}	V _{GS} = 0 V	I _{DS} = 10 mA	65			V
I _{DSS}	V _{GS} = 0 V	V _{DS} = 28 V			1	μA
I _{GSS}	V _{GS} = 20 V	V _{DS} = 0 V			1	μA
V _{GS(Q)}	V _{DS} = 28 V	I _D = 100 mA	2.0		5.0	V
V _{DS(ON)}	V _{GS} = 10 V	I _D = 3 A		0.7	0.9	V
G _{FS}	V _{DS} = 10 V	I _D = 3 A		3		mho
C _{ISS} *	V _{GS} = 0 V	V _{DS} = 28 V		169		pF
C _{OSS}	V _{GS} = 0 V	V _{DS} = 28 V		48		pF
C _{RSS}	V _{GS} = 0 V	V _{DS} = 28 V		2.7		pF

* Includes Internal Input Moscap.

DYNAMIC

Symbol	Test Conditions				Min.	Typ.	Max.	Unit
P _{OUT}	V _{DD} = 28 V	I _{DQ} = 800 mA		f = 960 MHz	120			W
G _{PS}	V _{DD} = 28 V	I _{DQ} = 800 mA	P _{OUT} = 120 W	f = 960 MHz	13	14		dB
η _D	V _{DD} = 28 V	I _{DQ} = 800 mA	P _{OUT} = 120 W	f = 960 MHz	50			%
Load mismatch	V _{DD} = 28 V	I _{DQ} = 800 mA	P _{OUT} = 120 W	f = 960 MHz	10:1			VSWR
	ALL PHASE ANGLES							

IMPEDANCE DATA

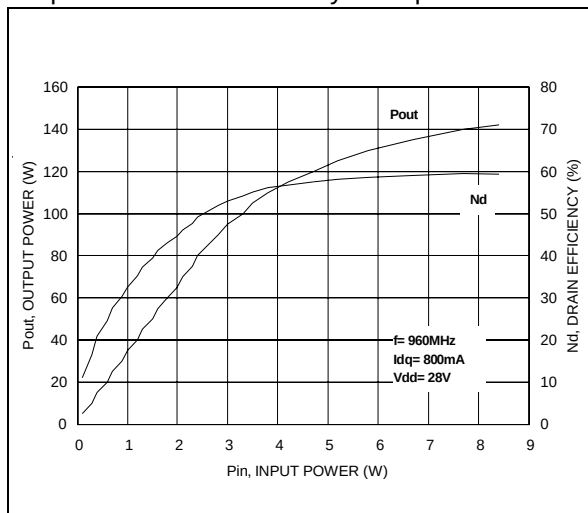


FREQ.	Z _{IN} (Ω)	Z _{DL} (Ω)
945 MHz	3.9 + j 4.9	3.26 - j 5.1
960 MHz	4.1 + j 4.6	3.24 - j 4.74
980 MHz	3.9 + j 5.2	3.27 - j 6.9

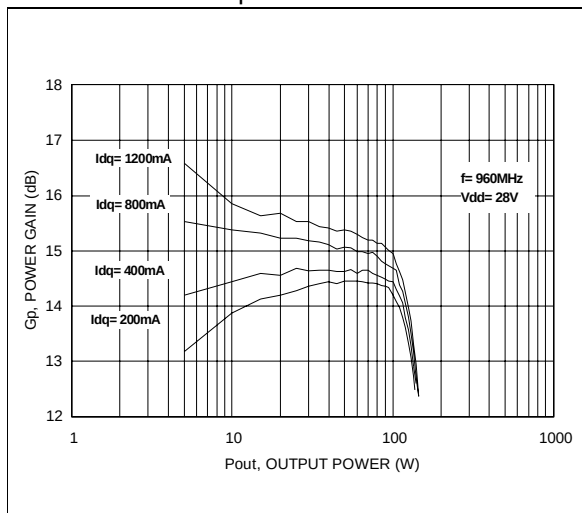
Measured gate and drain to drain respectively.

TYPICAL PERFORMANCE

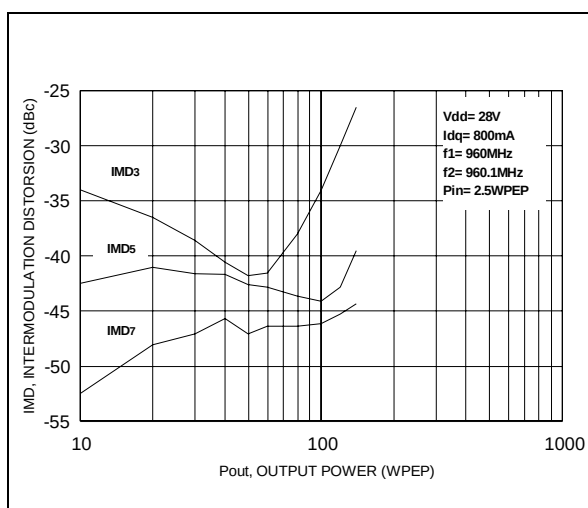
Output Power and Efficiency vs. Input Power



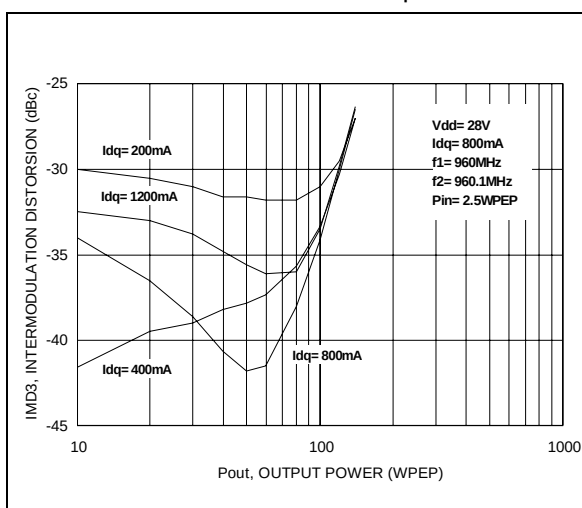
Power Gain vs. Output Power



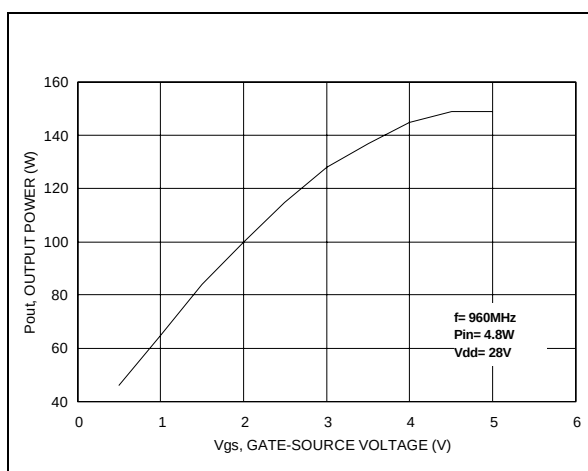
Intermodulation Distortion vs. Output Power



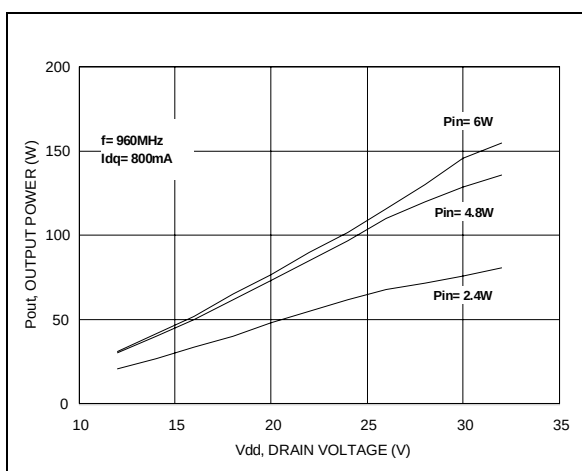
Intermodulation Distortion vs. Output Power



Output Power vs. Gate Voltage



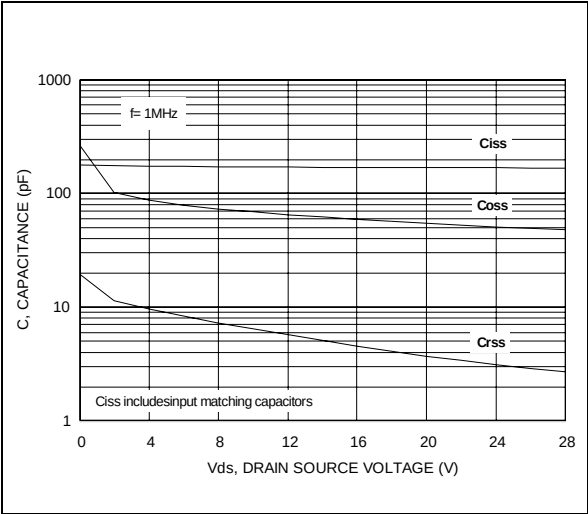
Output Power vs. Drain Voltage



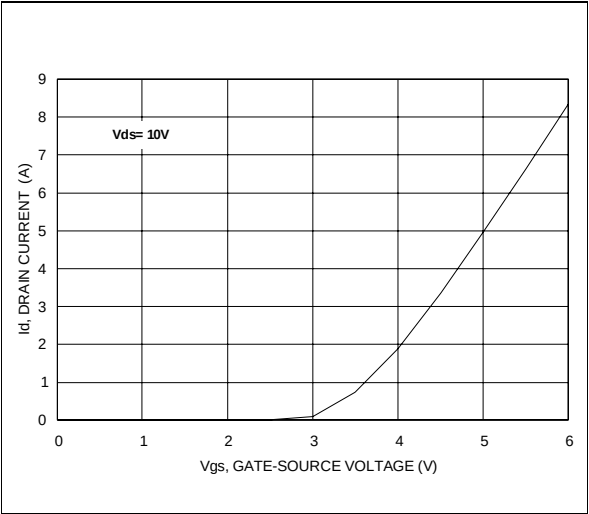
SD57120

TYPICAL PERFORMANCE

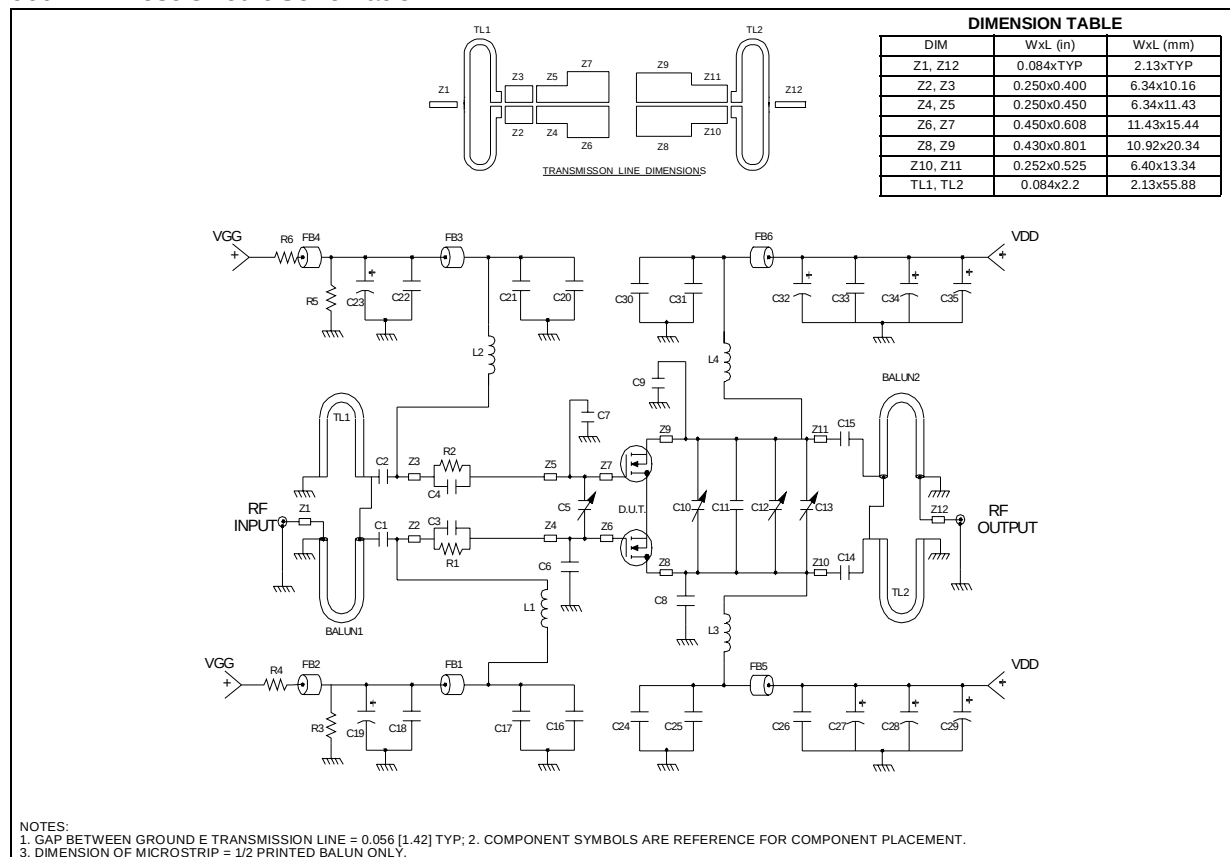
Capacitance vs. Drain Voltage



Drain Current vs. Gate Voltage



960 MHz Test Circuit Schematic

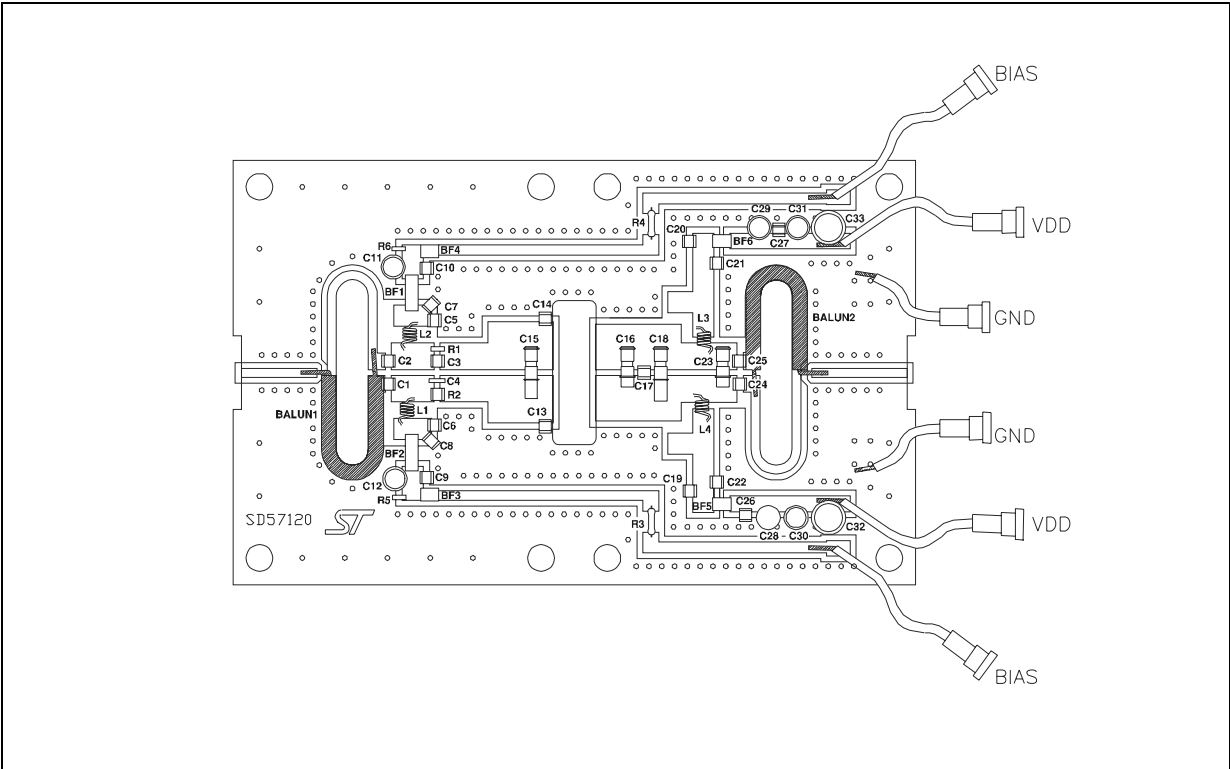


Ref. 7160637

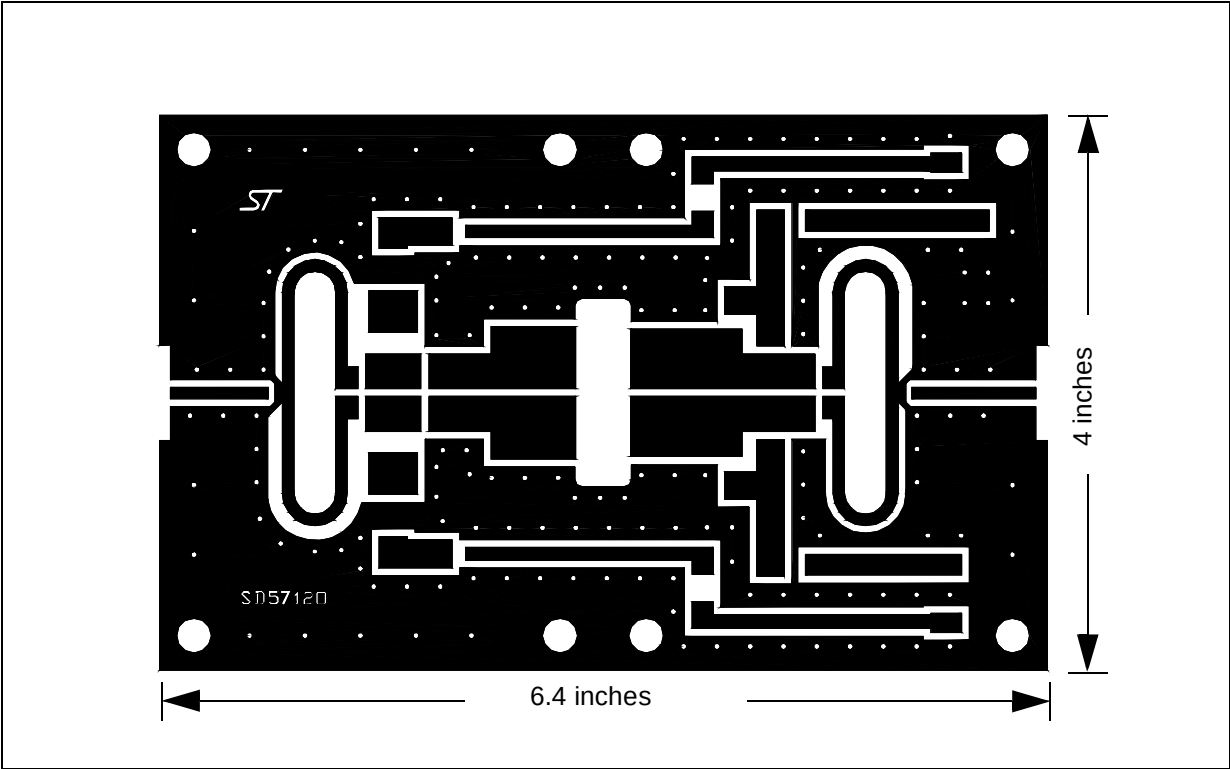
960 MHz Test Circuit Component Part List

COMPONENT	DESCRIPTION
BF1-BF4	SURFACE MOUNT EMI SHIELD BEAD
L1,L2,L3,L4	INDUCTOR, 3 TURN AIR-WOUND #20AWG ID=0.126[3.20] 24.7nH MAGNET WIRE
B1, B2	BALUN, 50 OHM SUCOFORM, OD 0.141. 2.20 LG COAXIAL CABLE OR EQUIVALENT
R1,R2	75 OHM 1 W SURFACE MOUNT CHIP RESISTOR
R3,R5	1.2 K OHM 1 W SURFACE MOUNT CHIP RESISTOR
R4,R6	1 K OHM 1 W SURFACE MOUNT CHIP RESISTOR
C1,C2,C14,C15	47 pF ATC 100B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C3,C4	42 pF ATC 100B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C5,C12	0.8-8 pF GIGATRIM VARIABLE CAPACITOR
C6,C7,C11	1.7 pF ATC 100B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C8,C9	5.6 pF ATC 100B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C10,C13	0.6-4.5 pF GIGATRIM VARIABLE CAPACITOR
C16,C17,C20,C21,C24,C25,C30,C31	300 pF ATC 700B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C18,C22	10000 pF ATC 200B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C19,C23,C27,C28,C32,C34	10 µF, 50 V ALUMINUM ELECTROLYTICS RADIAL LEAD CAPACITOR
C26,C33	20000 pF ATC 900B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C29,C35	220 µF, 50 V ALUMINUM ELECTROLYTICS RADIAL LEAD CAPACITOR
BOARD	ULTRA LAM 2000. 0.030" THK, $\epsilon_r = 2.55$, 2 O ₂ ED CU BOTH SIDES

960 MHz Production Test Fixture



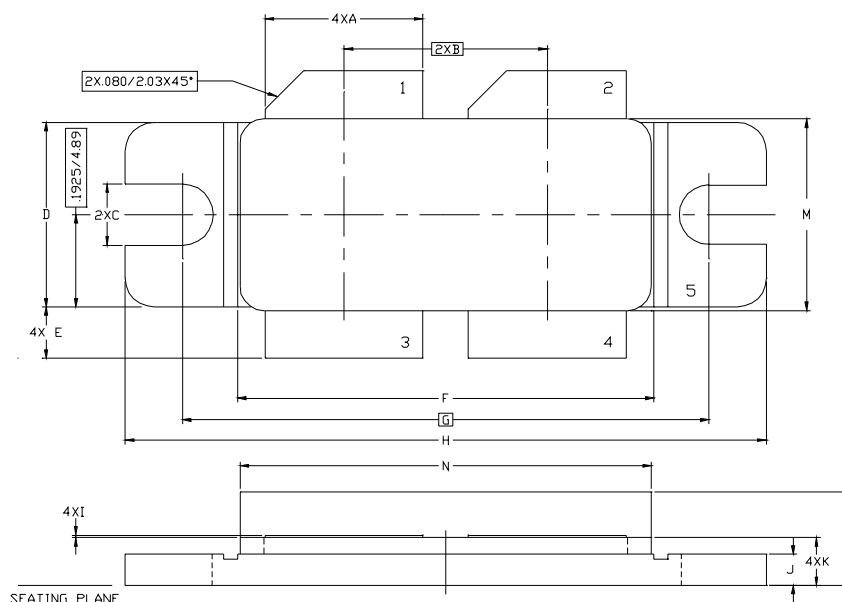
960 MHz Test Circuit Photomaster



Ref. 7160637

M252 (.400 x .860 4L BAL N/HERM W/FLG) MECHANICAL DATA

DIM.	mm			Inch		
	MIN.	TYP.	MAX	MIN.	TYP.	MAX
A	8.13		8.64	.320		.340
B		10.80			.425	
C	3.00		3.30	.118		.130
D	9.65		9.91	.380		.390
E	2.16		2.92	.085		.115
F	21.97		22.23	.865		.875
G		27.94			1.100	
H	33.91		34.16	1.335		1.345
I	0.10		0.15	.004		.006
J	1.52		1.78	.060		.070
K	2.36		2.74	.093		.108
L	4.57		5.33	.180		.210
M	9.96		10.34	.392		.407
N	21.64		22.05	.852		.868



Controlling dimension: Inches

1022783C

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